

Transforming Ideas to Reality

MAJOR CHALLENGES

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> Memory access

Compute

Carbon Nanotube FET

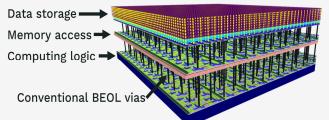


Materials & Integration Thrust : Three Dimensional Monolithic System on a Chip (3DSoC)



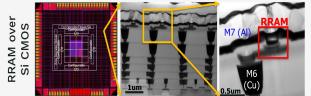
3DSOC: OUR APPROACH

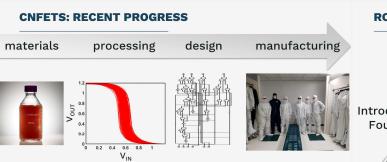
- Monolithic 3D Integration
 - Fine-grained integration: logic + memory



RRAM TECHNOLOGY

- Dense on-chip non-volatile memory
 - Simple
 - BEOL compatible
 - Path to 3D RRAM





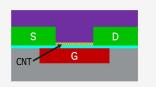
Si-compatible; >99.99% purity

Robust doping: Immune to CNFET CMOS metallic CNTs



CNFET TECHNOLOGY

- 90 nm technology node
 - Relaxes technology requirements
 - BEOL compatible
 - Fully complementary





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(CNTs)

ENABLING TECHNOLOGIES

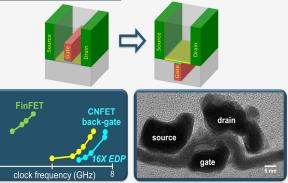
- Requires low temperature fabrication
- Challenging with conventional silicon CMOS

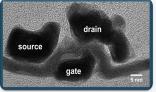


CNFET TECHNOLOGY

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TEAM



Program + system integration

stand-up CNFET, RRAM modules

• demo monolithic 3D ICs

develop MPW offering



 RRAM (optimize, transfer, PDK • monolithic 3D system design evaluation (benchmarking)



 improving CNT material high-volume CNT production



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facilities

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